



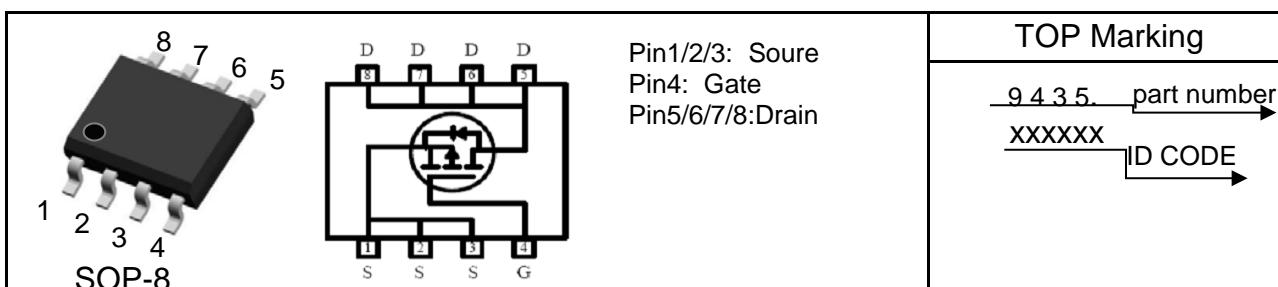
P-Channel Enhancement-Mode MOSFET (-30V, -5.3A)

PRODUCT SUMMARY

V_{DSS}	I_D	$R_{DS(on)}$ (mΩ)TYP
-30V	-5.3A	50 @ $V_{GS} = -10$ V, $I_D = -5.3$ A
		70 @ $V_{GS} = -4.5$ V, $I_D = -4.2$ A

Features

- Advanced Trench Process Technology
- High Density Cell Design for Ultra Low On-Resistance
- Fully Characterized Avalanche Voltage and Current
- Improved Shoot-Through FOM
- Ordering information : ES9435 (Lead (Pb) -free and halogen-free)

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current (Continuous)	-5.3	A
I_{DM}	Drain Current (Pulsed) ^a	-20	A
P_D	Total Power Dissipation @ $T_A=25^\circ\text{C}$	2.5	W
I_S	Maximum Diode Forward Current	-2.6	A
T_j, T_{stg}	Operating Junction and Storage Temperature Range	-55 to +150	°C
R_{QJA}	Thermal Resistance Junction to Ambient (PCB mounted) ^b	60	°C/W

a: Repetitive Rating: Pulse width limited by the maximum junction temperature.

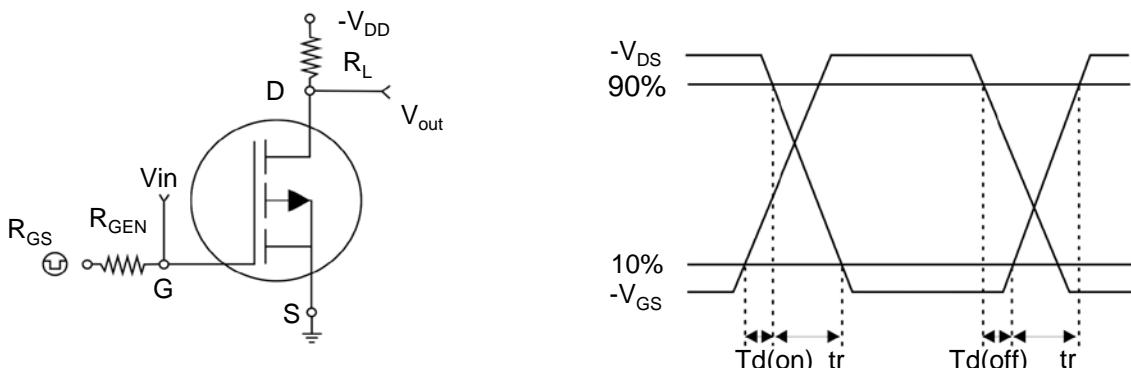
b: 1-in² 2oz Cu PCB board



Electrical Characteristics ($T_A=25^\circ\text{C}$, unless otherwise noted)

Symbol	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
• Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$	-30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{\text{DS}}=-30\text{V}, V_{\text{GS}}=0\text{V}$	-	-	-1	μA
I_{GSS}	Gate-Body Leakage Current	$V_{\text{GS}}=\pm 20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	± 100	nA
• On Characteristics						
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=-250\mu\text{A}$	-1	-1.4	-2	V
$R_{\text{DS(on)}}$	Drain-Source On-State Resistance	$V_{\text{GS}}=-10\text{V}, I_{\text{D}}=-5.3\text{A}$	-	50	60	$\text{m}\Omega$
		$V_{\text{GS}}=-4.5\text{V}, I_{\text{D}}=-4.2\text{A}$	-	70	90	
• Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{\text{DS}}=-15\text{V}, V_{\text{GS}}=0\text{V}, f=1\text{MHz}$	-	553	-	PF
C_{oss}	Output Capacitance		-	93	-	
C_{rss}	Reverse Transfer Capacitance		-	63	-	
• Switching Characteristics						
Q_g	Total Gate Charge	$V_{\text{DS}}=-15\text{V}, I_{\text{D}}=-5.3\text{A}, V_{\text{GS}}=-10\text{V}$	-	9.86	-	nC
Q_{gs}	Gate-Source Charge		-	3.28	-	
Q_{gd}	Gate-Drain Charge		-	1.92	-	
$t_{\text{d(on)}}$	Turn-on Delay Time	$V_{\text{DD}}=-15\text{V}, RL=5\Omega, ID=-3\text{A}, V_{\text{GEN}}=-10\text{V}, RG=6\Omega$	-	11	-	nS
t_r	Turn-on Rise Time		-	2.85	-	
$t_{\text{d(off)}}$	Turn-off Delay Time		-	23	-	
t_f	Turn-off Fall Time		-	3.2	-	
• Drain-Source Diode Characteristics						
V_{SD}	Drain-Source Diode Forward	$V_{\text{GS}}=0\text{V}, I_{\text{S}}=-2.6\text{A}$	-	-	-1.3	V

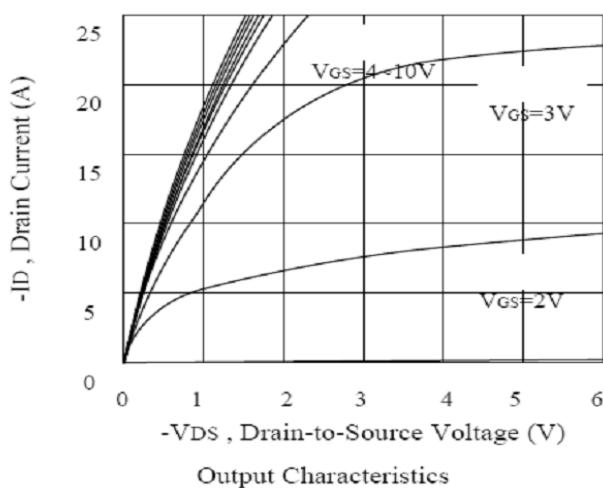
Note: Pulse Test: Pulse Width $\leq 300\text{us}$, Duty Cycle $\leq 2\%$



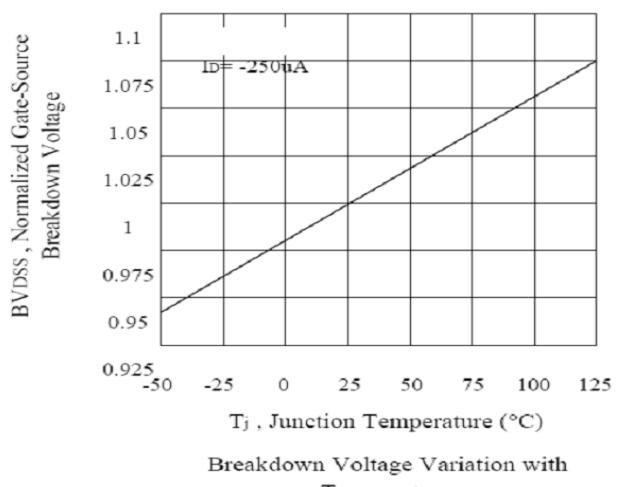
Switching Test Circuit and Swithcing Waveforms



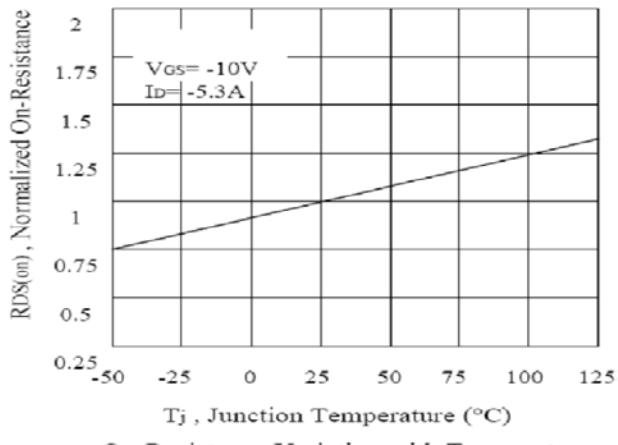
Typical Characteristics Curves (Ta=25°C, unless otherwise note)



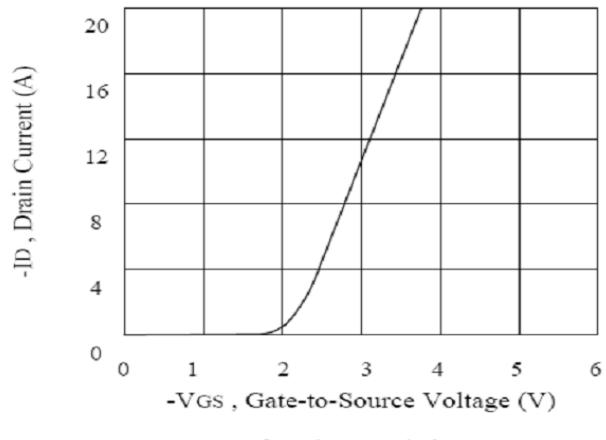
Output Characteristics



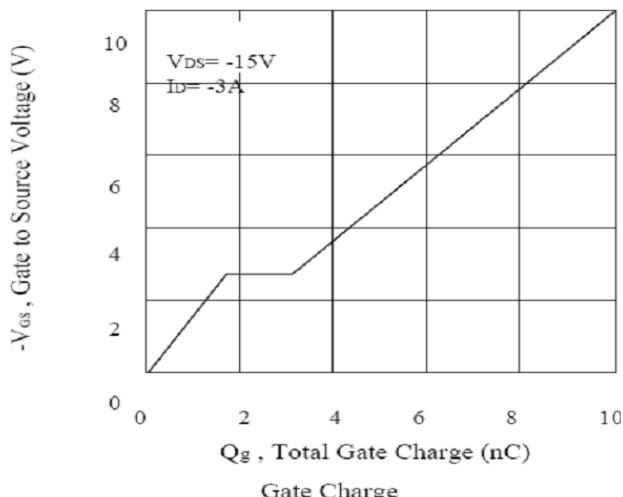
Breakdown Voltage Variation with Temperature



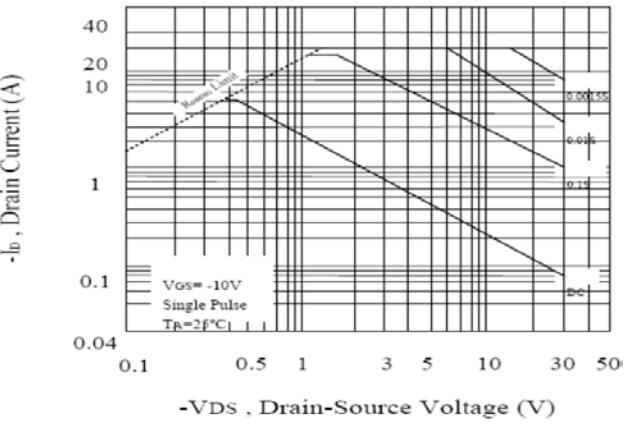
On-Resistance Variation with Temperature



Transfer Characteristics



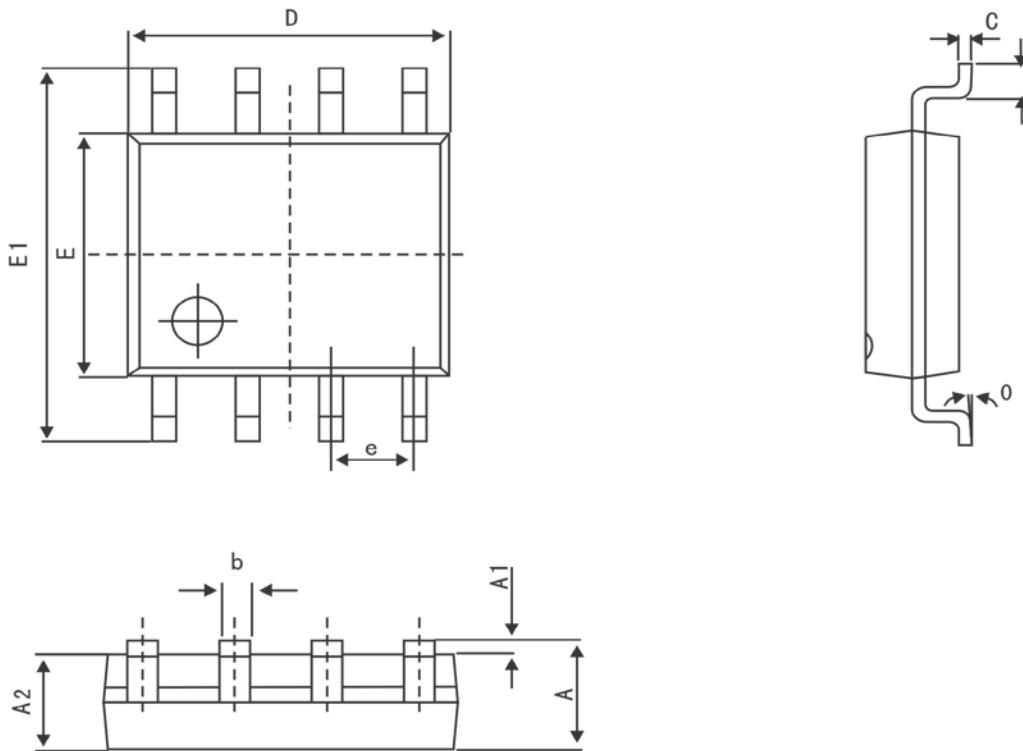
Gate Charge



Maximum Safe Operating Area



sop-8 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters (MM)		Dimensions In Inches (MIL)	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.700	5.100	0.185	0.201
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by Eternal Semiconductor manufacturer:

Other Similar products are found below :

[614233C](#) [648584F](#) [MCH3443-TL-E](#) [MCH6422-TL-E](#) [FDPF9N50NZ](#) [NTNS3A92PZT5G](#) [IRFD120](#) [IRFF430](#) [JANTX2N5237](#) [2N7000](#)
[AOD464](#) [2SK2267\(Q\)](#) [2SK2545\(Q,T\)](#) [405094E](#) [423220D](#) [MIC4420CM-TR](#) [VN1206L](#) [614234A](#) [715780A](#) [751625C](#)
[IPS70R2K0CEAKMA1](#) [BSF024N03LT3 G](#) [PSMN4R2-30MLD](#) [TK31J60W5,S1VQ\(O](#) [2SK2614\(TE16L1,Q\)](#) [DMN1017UCP3-7](#)
[EFC2J004NUZTDG](#) [FCAB21350L1](#) [P85W28HP2F-7071](#) [DMN1053UCP4-7](#) [NTE2384](#) [NTE2969](#) [NTE6400A](#) [DMC2700UDMQ-7](#)
[DMN2080UCB4-7](#) [DMN61D9UWQ-13](#) [US6M2GTR](#) [DMN31D5UDJ-7](#) [SSM6P54TU,LF](#) [DMP22D4UFO-7B](#) [IPS60R3K4CEAKMA1](#)
[DMN1006UCA6-7](#) [DMN16M9UCA6-7](#) [STF5N65M6](#) [IRF40H233XTMA1](#) [IPSA70R950CEAKMA1](#) [IPSA70R2K0CEAKMA1](#) [STU5N65M6](#)
[C3M0021120D](#) [DMN6022SSD-13](#)